

Electron Spin Resonance of Graphite and Graphene

C. Sewell, 1 A. Mahjoub, 2 A. Takuto, 2 and Y. Ochiai 3

¹NanoJapan Program, Rice University, Houston, Texas and Department of Physics and Engineering Physics, University of Tulsa, Oklahoma

²Department of Nanomaterial Science, Chiba University, Chiba, Japan



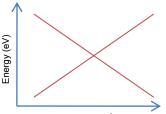
Introduction

Gaphene-

- Zero effective mass of electrons due band structure
 - Causes high electron mobility (100 times that of silicon at room temp)
- ❖Small spin-orbit coupling of carbon atoms
 - ➤ Highly desirable in spintronic devices



Graphene band structure

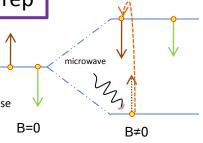


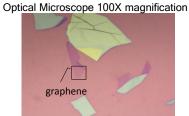
ESR- wavevector \underline{k}

- ❖Used to explore spin properties of electrons in graphite and graphene
- Will determine g-factor using this method

Methods and Sample Prep

- ❖Sample subjected to constant 9.2 GHz microwave frequency *v*
- ❖DC magnetic field B_0 scans over sample
- ❖When B_0 satisfies $\hbar v = g\mu_B B_0$ electrons absorb microwave photon energy
- ❖Lock-in amplifier separates signal from noise
- Produces absorption peaks as function of magnetic field strength
- ❖Used kish and HOPG graphite
- ❖ Prepared sample using exfoliation and scraping techniques
- ❖Light pink areas in right photo are graphene
- ❖Glue and green areas are graphite





Results

0.50

0.25

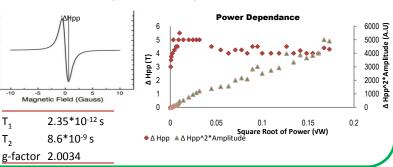
-0.25

Thin graphene Thick graphite

Graphene

- ❖ Field based ESR insufficiently sensitive to detect the microwave absorption of graphene
 - Size of sample produced by exfoliation is to small
 - Interference from surrounding graphite dwarfed the graphene absorption

Graphite Power Dependence-



Conclusion

- ❖Detected graphite absorption spectrum
- ❖ Derived graphite g-factor
- ❖Calculated T₁ and T₂ relaxation times
- ❖Will implement low temperature aspect to power dependant testing
- ❖Must use resistive techniques in order to determine graphene g-factor





